**Progress in Applied Surface, Interface
   and Thin Film Science 2012**

**SURFINT-SREN III, 14-19. May 2012**

**Invited speakers**

**� Dietrich R.T. Zahn, Chemnitz University of Technology, Chemnitz, Germany
   Ferromagnetic/Organic Interfaces for Spintronic Applications

� Hikaru Kobayashi, Institute of Scientific and Industrial Research and CREST,
   Japan Science and Technology Agency, Osaka University, Japan
   New surface technologies for improvement of conversion efficiencies of crystalline Si solar cells

� Shigeru Masuda, Department of Basic Science, The University of Tokyo, Japan
   A new characterization of electronic states at organic�metal interface

� Toshiaki Makabe, Keio University, Yokohama, Japan
   Influence of gas heating on a plasma structure in an rf-microcell in Ar

� Thomas Chass�, Institute f�r Physikalische Chemie, Universit�t T�bingen, T�bingen, Germany
   Electronic interactions at transition metal phthalocyanine - metal interfaces

� Helena Gleskova, Department of Electronic and Electrical Engineering, University of Strathclyde,
   Glasgow, United Kingdom
   Ultra-thin, inorganic-organic dielectric bi-layers as gate dielectrics in organic thin-film transistors

� Shigeki Imai, Institute of Scientific and Industrial Research and CREST,
   Japan Science and Technology Agency, Osaka University, Japan
   Thin Film Transistors (TFT) with Stacked Gate Oxide Formed by the Nitric Acid Oxidation of Si
   (NAOS) Method and Application to Low Power Liquid Crystal Display (LCD) and Ring Oscillator

� Taketoshi Matsumoto, Institute of Scientific and Industrial Research and CREST,
   Japan Science and Technology Agency, Osaka University, Japan
   Application of Ultra-thin SiO2 Layer Formed by the Nitric Acid Oxidation of Si
   (NAOS) Method to Stacked Gate Oxide in Thin Film Transistors (TFT)

� Heike Angermann, Helmholtz-Zentrum f�r Materialien und Energie GmbH,
   Institute f�r Silizium-Photovoltaik, Berlin, Germany
   Interface states and recombination losses on textured Si substrates after wet-chemical
   conditioning

� Jozef Nov�k, Institute of Electrical Engineering SAS, Bratislava, Slovakia
   ZnO/GaP Nanowires Prepared by Combination of MOVPE growth and RF sputtering

� �tefan Chromik, Institute of Electrical Engineering SAS, Bratislava, Slovakia
   Significant increasing of onset temperature of FM transition in LSMO thin films

� Giovanni Piero Pepe, Universita di Napoli �Federico II�, Napoli, Italy
   Self-assembled plasmonic arrays based on block-copolymer nanostructures:
   transport and optical properties

� Roman Sobolewski, University of Rochester, Rochester, USA, and
   Institute of Electron Technology, Warsaw, Poland
   Femtosecond time-resolved studies of carrier and spin dynamics in all-oxide
   superconductor/ferromagnet proximitized nanobilayers

� Zsolt Jozsef Horv�th, �buda University and Research Institute for
   Technical Physics and Materials Science HAS, Budapest, Hungary
   Silicon nitride based non-volatile memory structures with embedded
   semiconductor nanocrystals

� Katsuhiro Akimoto, Tsukuba University, Tsukuba, Ibaraki, Japan
   Non-radiative recombination centers in Cu(In,Ga)Se2

� Kazuyuki Edamoto, Rikkyo University, Toshima, Tokyo, Japan
   The electronic properties of transition metal phosphide surfaces:
   Angle-resolved and resonant photoemission studies

� Peter �vec, Institute of Physics SAS, Bratislava, Slovakia
   Formation, structure and properties of mono, bi and tri-layered rapidly quenched ribbons

� Aarne Kasikov, Institute of Physics, University of Tartu, Tartu, Estonia
   Transmission spectrometry vs spectral ellipsometry: Bruggeman EMA layer revisited

� Ratiba Outemzabet, Universite des Sciences et de la Technologie Honari Boumedienne,
   Alger, Alg�ria
   Competition and transition between oxides and silicon hydrides at anodised Silicon/HF interface

� Yossi Paltiel, Faculty of Science, The Hebrew University, Jerusalem, Israel
   Quantum Devices Using Monolayer Hybrid Surfaces

� Sabu Thomas, Centre for Nanoscience and Nanotechnology, School of Chemical Sciences,
   Mahatma Gandhi University, Kottayam, Kerala, India
   Micro and Nanostructured Epoxy based Blends for Supertoughnes

� Stanislav Jure�ka, University of �ilina, Slovak Republic
   Physics-based models for evaluating of MOS capacitors with ultrathin oxide layer

� Uros Cvelbar, Jozef Stefan Institute, Ljubljana, Slovenia
   Large scale production of metal-oxide nanowires for next step

� Jaroslav Kov��, Faculty of Electrical Engineering and Information Technology,
   Institute of Electronics and Photonics of Slovak University of Technology, Bratislava,
   Slovak Republic
   Micro Raman spectroscopy diagnostics of semiconductor structures and devices

� Amarjeet Kaur, Department of Physics and Astrophysics, University of Delhi, Delhi, India
   Donor-Acceptor nanoparticles interactions in the organic solar cell devices

� Michal Ru�insk�, Institute of Power and Applied Electrical Engineering of FEEIT of SUT,
   Bratislava, Slovak Republic
   History and the Present Time of Solar Car Races in the World

� Renato S. Gonnelli, Dipartimento di Scienza Applicata e Tecnologia, Politecnico di Torino,
   Torino, Italy
   Huge field-effect surface charge injection and conductance modulation in metal thin films by
   electrochemical gating

� Jun Xu, Department of Microelectronics and Optoelectronics, School of Electronic Science and
   Engineering, Nanjing University, Nanjing, China
   Preparation of size-controllable Si quantum dot multilayers for photonic and photovoltaic
   applications

� Pavel �utta, New Technologies - Research Center, University of West Bohemia, Plze�,
   Czech Republic
   Microstructure determination of microcrystalline-Si:H films analysing the breadths of
   diffraction and spectral lines of XRD, FTIR and Raman spectroscopies

� Vitaly L. Alperovich, Institute of Semiconductor Physics, Novosibirsk, Russia
   Atomic smoothing of GaAs surface in equilibrium conditions

� Cesare Frigeri, CNR-IMEM Institute, Parma, Italy

� Benoit Jouault, CNRS, Universit� Montpellier, Montpellier, France
   Surface graphene films on SiC with application to the metrology of quantum resistances

� Alexander �atka, FEEIT Slovak University of Technology, Bratislava, Slovak Republic
   EBIC at Schottky nanocontact on GaN epitaxial layers**